

ZXTN25012EFH

12V, SOT23, NPN medium power transistor

Summary

$BV_{CEO} > 12V$

$BV_{ECX} > 6V$

$h_{FE} > 500$

$I_{C(cont)} = 6A$

$V_{CE(sat)} < 32mV @ 1A$

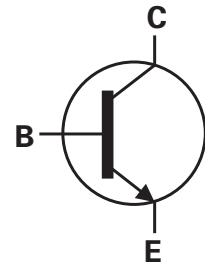
$R_{CE(sat)} = 23m\Omega$

$P_D = 1.25W$



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

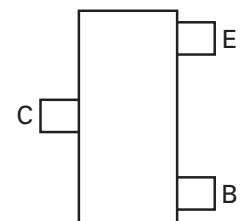


Features

- High power dissipation SOT23 package
- High peak current
- Very high gain
- Low saturation voltage
- 6V reverse blocking voltage

Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters



Pinout - top view

Ordering information

| Device | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|--------------------|-----------------|-------------------|
| ZXTN25012EFHTA | 7 | 8 | 3,000 |

Device marking

1C3

ZXTN25012EFH

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|--|----------------|--------------|------------|
| Collector-base voltage | V_{CBO} | 20 | V |
| Collector-emitter voltage | V_{CEO} | 12 | V |
| Emitter-collector voltage (reverse blocking) | V_{ECX} | 6 | V |
| Emitter-base voltage | V_{EBO} | 7 | V |
| Continuous collector current ^(c) | I_C | 6 | A |
| Base current | I_B | 1 | A |
| Peak pulse current | I_{CM} | 15 | A |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$ Linear derating factor | P_D | 0.73 5.84 | W mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$ Linear derating factor | P_D | 1.05 8.4 | W mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$ Linear derating factor | P_D | 1.25 9.6 | W mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$ Linear derating factor | P_D | 1.81 14.5 | W mW/°C |
| Operating and storage temperature range | T_j, T_{stg} | - 55 to 150 | °C |

Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 171 | °C/W |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 119 | °C/W |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 100 | °C/W |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 69 | °C/W |

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

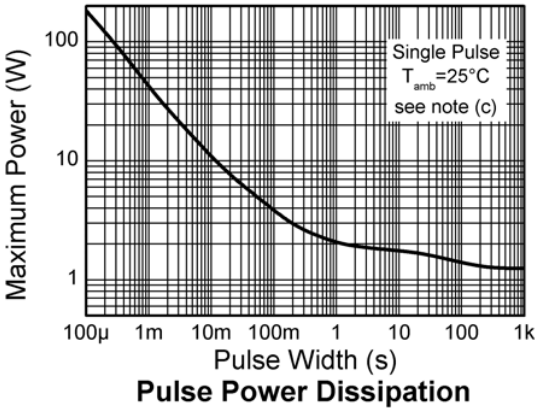
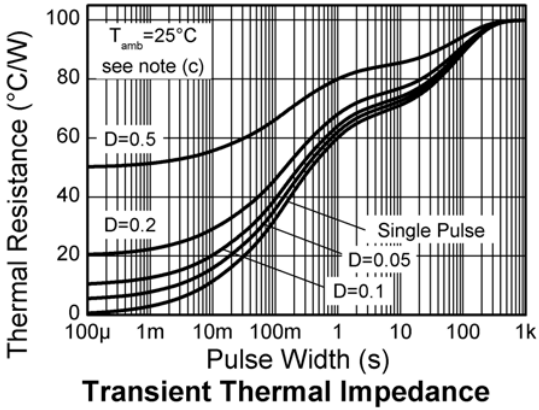
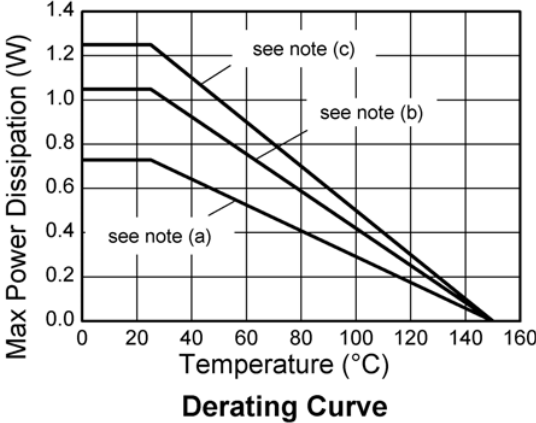
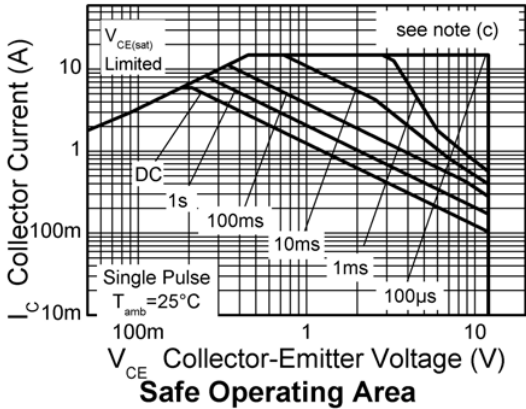
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

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Characteristics



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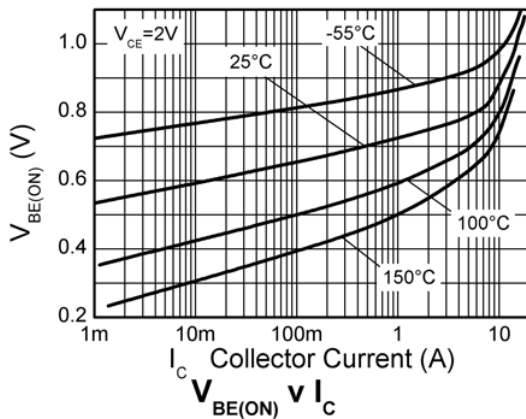
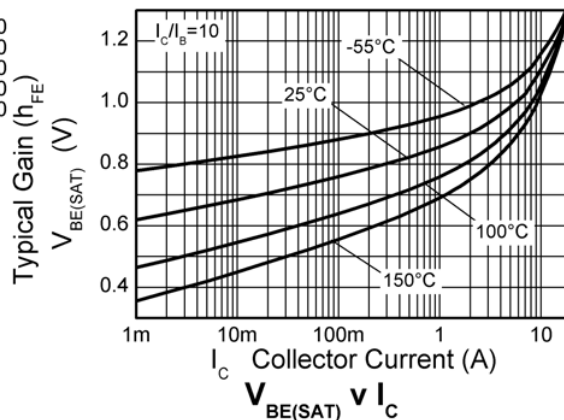
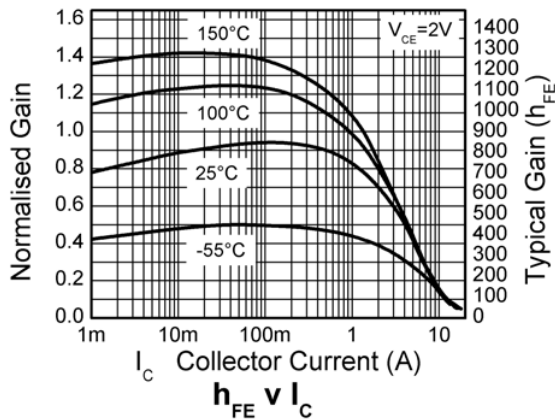
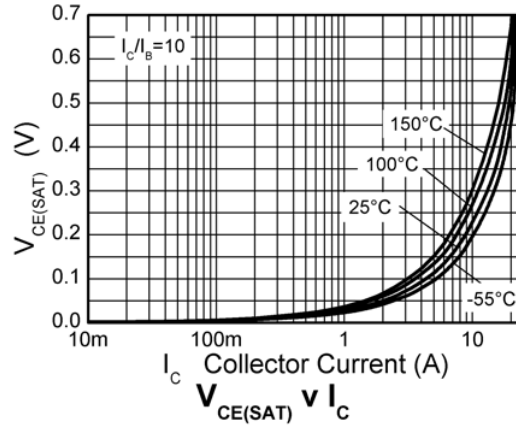
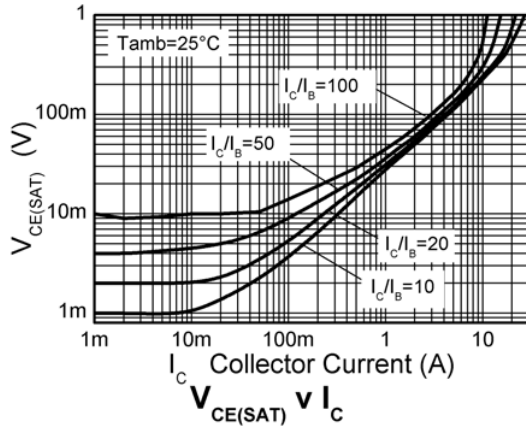
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--|---------------|-------------------------|-------------------------|-----------------------|----------------------|---|
| Collector-base breakdown voltage | BV_{CBO} | 20 | 40 | | V | $I_C = 100\mu\text{A}$ |
| Collector-emitter breakdown voltage (base open) | BV_{CEO} | 12 | 17 | | V | $I_C = 10\text{mA}^{(*)}$ |
| Emitter-base breakdown voltage | BV_{EBO} | 7 | 8.3 | | V | $I_E = 100\mu\text{A}$ |
| Emitter-collector breakdown voltage (reverse blocking) | BV_{ECX} | 6 | 8.0 | | V | $I_E = 100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$ |
| Emitter-collector breakdown voltage (base open) | BV_{ECO} | 4.5 | 5.5 | | V | $I_E = 100\mu\text{A}$, |
| Collector-base cut-off current | I_{CBO} | | <1 | 50 0.5 | nA μA | $V_{CB} = 20\text{V}$ $V_{CB} = 20\text{V}$, $T_{amb} = 100^{\circ}\text{C}$ |
| Emitter-base cut-off current | I_{EBO} | | <1 | 50 | nA | $V_{EB} = 5.6\text{V}$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | | 28 45 60 160 | 32 55 75 190 | mV mV mV mV | $I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$ $I_C = 1\text{A}$, $I_B = 10\text{mA}^{(*)}$ $I_C = 2\text{A}$, $I_B = 40\text{mA}^{(*)}$ $I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$ |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | | 920 | 1000 | mV | $I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$ |
| Base-emitter turn-on voltage | $V_{BE(on)}$ | | 800 | 900 | mV | $I_C = 6\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Static forward current transfer ratio | h_{FE} | 500 500 300 40 | 800 750 460 55 | 1500 | | $I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 4\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 15\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Transition frequency | f_T | | 260 | | MHz | $I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$ |
| Output capacitance | C_{OBO} | | 25.6 | 35 | pF | $V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$ |
| Delay time | t_d | | 70.9 | | ns | $V_{CC} = 10\text{V}$. |
| Rise time | t_r | | 69.8 | | ns | $I_C = 1\text{A}$, |
| Storage time | t_s | | 233 | | ns | $I_{B1} = I_{B2} = 10\text{mA}$. |
| Fall time | t_f | | 71.6 | | ns | |

NOTES:

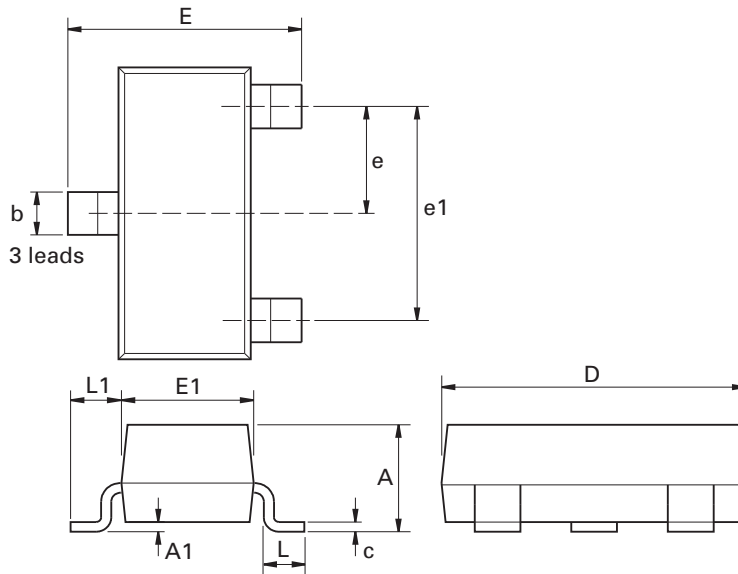
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTN25012EFH

Package outline - SOT23



| Dim. | Millimeters | | Inches | | Dim. | Millimeters | | Inches | |
|------|-------------|------|-----------|-------|------|-------------|------|-----------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | - | 1.12 | - | 0.044 | e1 | 1.90 NOM | | 0.075 NOM | |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 | E | 2.10 | 2.64 | 0.083 | 0.104 |
| b | 0.30 | 0.50 | 0.012 | 0.020 | E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| c | 0.085 | 0.20 | 0.003 | 0.008 | L | 0.25 | 0.60 | 0.0098 | 0.0236 |
| D | 2.80 | 3.04 | 0.110 | 0.120 | L1 | 0.45 | 0.62 | 0.018 | 0.024 |
| e | 0.95 NOM | | 0.037 NOM | | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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